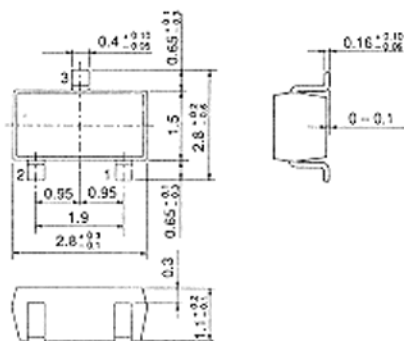


## 2SC2462

SILICON NPN EPITAXIAL  
LOW FREQUENCY AMPLIFIER



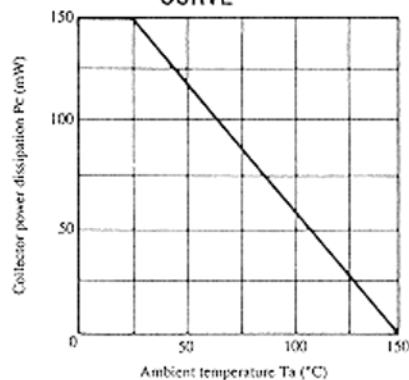
(MPAK)

1. Emitter
  2. Base
  3. Collector
- (Dimensions in mm)

### ■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC2462	Unit
Collector to base voltage	V <sub>CB0</sub>	50	V
Collector to emitter voltage	V <sub>CE0</sub>	40	V
Emitter to base voltage	V <sub>EB0</sub>	5	V
Collector current	I <sub>C</sub>	100	mA
Emitter current	I <sub>E</sub>	-100	mA
Collector power dissipation	P <sub>C</sub>	150	mW
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

### MAXIMUM COLLECTOR DISSIPATION CURVE



### ■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0	50	—	—	V
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1mA, R <sub>BE</sub> = ∞	40	—	—	V
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0	5	—	—	V
Collector cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> = 30V, I <sub>E</sub> = 0	—	—	0.5	μA
Emitter cutoff current	I <sub>EB0</sub>	V <sub>EB</sub> = 2V, I <sub>C</sub> = 0	—	—	0.5	μA
DC current transfer ratio	h <sub>FE</sub> *	V <sub>CE</sub> = 12V, I <sub>C</sub> = 2mA	100	—	500	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA	—	—	0.2	V
Base to emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = 12V, I <sub>C</sub> = 2mA	—	—	0.75	V

\* The 2SC2462 is grouped by h<sub>FE</sub> as follows.

Grade	B	C	D
Mark	LB	LC	LD
h <sub>FE</sub>	100 to 200	160 to 320	250 to 500

■ See characteristic curves of 2SC458 (LG)